



GENERAL DESCRIPTION

The PT4121E is a high efficiency step-down controller. It is designed to operate in continuous conduction mode and drive single or multiple series connected LED efficiently from a voltage source higher than the total LED chain voltage. It operates with a wide input voltage from 6V to 60V and provides an externally adjustable output current.

The PT4121E includes a high-side output current sense circuit, which uses an external resistor to set the nominal average output current, and a dedicated DIM input accepts either a DC voltage or PWM dimming.

The PT4121E is available in SOT23-6 or SOP-8 packages.

FEATURES

- Simple low parts count
- Wide input voltage range: 6V to 60V
- High efficiency (up to 97%)
- Single pin on/off and brightness control using DC Voltage or PWM
- Up to 1MHz switching frequency
- Adjustable Constant LED Current
- Typical 3% output current accuracy
- High-Side Current Sense
- Hysteretic Control: No need compensation
- Inherent R_{CS} open protection
- Inherent open-circuit LED protection
- Inherent short-circuit LED protection
- Over Temperature Protection

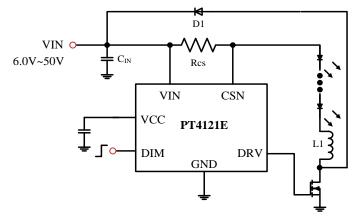
APPLICATIONS

- Low voltage halogen replacement LEDs
- Automotive/Decorative lighting
- Low voltage industrial lighting
- LED back-up lighting
- Signs/Emergency lighting
- SELV lighting
- LCD TV backlighting

ORDERING INFORMATION

PACKAGE	TEMPERATURE	ORDERING PART	TRANSPORT	MARKING
SOT23-6	-40 °C to 125 °C	NUMBER PT4121EE23F	MEDIA Tape and Reel 3000 units	4121E
SOP-8	-40℃ to 125℃	PT4121EESOH	Tape and Reel 4000 units	PT4121E xxxxxX

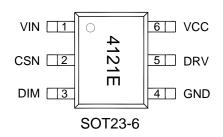
TYPICAL APPLICATION CIRCUIT

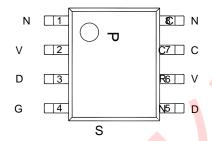


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PIN ASSIGNMENT





PIN DESCRIPTIONS

PIN No. SOP-8	PIN No. SOT23-6	PIN NAMES	DESCRIPTION
1		NC	Not connected.
2	6	VCC	Internal Regulator Output. Connect a 1µF decoupling cap from this pin to ground.
3	5	DRV	Gate-Driver Output. Connect this pin to the gate of the external MOSFET.
4	4	GND	Signal and power ground. Connect directly to ground plane.
5	3	DIM	Logic level dimming input. Drive DIM low to turn off the current regulator. Drive DIM high to enable the current regulator.
6	1	VIN	Input Supply Pin. Connect a decoupling capacitor from VIN pin to GND.
7	2	CSN	LED Current Sense Input. Connect a current-sense resistor that programs LED average current to the VIN pin.
8		NC	Not connected.

ABSOLUTE MAXIMUM RATINGS (note1)

SYMBOL	PARAMETER	VALUE	UNIT	
V _{IN}	Supply Voltage	-0.3~60	V	
CSN	Current sense input (Respect to VIN)	+0.3~(-6.0)	V	
V _{I/O}	Other I/O PIN Input Voltage	-0.3~6	V	
	SOT23-6 Thermal Resistance	220	°C /W	
θ_{JA}	SOP-8 Thermal Resistance	145	°C /W	
T _J	Junction Temperature	150	°C	
T _{OP}	Operating Temperature Range	-40~125	°C	
T _{STG}	Storage Temperature Range	-55 to 150	°C	
·	ESD Susceptibility (Note 2)	2	kV	

Note 1: Exceeding these Absolute Maximum Ratings may damage the device. Recommended Operating Range indicates conditions for which the device is functional. Electrical Characteristics state DC and AC electrical specifications under particular test conditions which guarantee specific performance limits. This assumes that the device is within the Operating Range. Specifications are not guaranteed for parameters where no limit is given, however, the typical value is a good indication of device performance.

Note 2: Human body model, 100pF discharged through a $1.5k\Omega$ resistor.



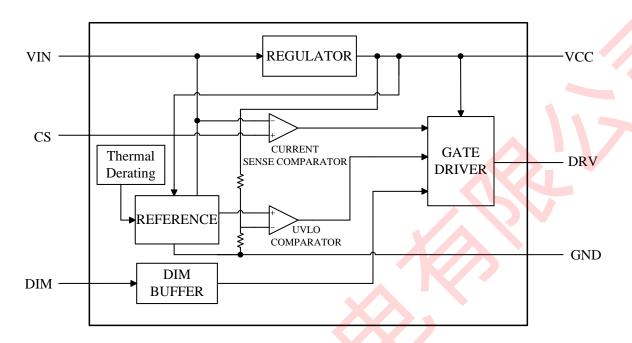
ELECTRICAL CHARACTERISTICS (Note 3)

The following specifications apply for V_{IN}=24V, T_A=25 °C, unless specified otherwise.

V _{IN} Input Voltage	SYMBOL	ITEMS	CONDITIONS		Min.	Тур.	Max.	UNIT
V _{UNLO, HYS} UVLO hysterisis VCC falling 0.3 V F _{SW} Max. Switching Frequency 1 MHz Current Sense V _{CSN} Current sense threshold voltage V _{IN} -V _{CSN} Nominal 194 200 206 mV V _{CSN, HYS} Sense threshold hysteresis ±15 % % ½ % ½ % ½ % ½ % ½ % ½ % ½ % ½ % ½ % ½ % ½ ½ % ½ % ½ ½ % ½ ½ % ½ ½ % ½ ½ ½ % ½ ½ ½ % ½ ½ ½ ½ ½ ½ ½ ½ ¾ ½ ½ ¾ ¾ ¾ ¾ ¾ ¾ ¾ ¾ ¾ ¾ ¾ ¾ ¾ ¾ ¾ ¾ ¾	V _{IN}	Input Voltage			6		60	V
F _{SW} Max. Switching Frequency 1 1 MHz	VCC	Internal Regulated Voltage			4.5	5.0	5.5	V
Current Sense V _{CSN} Current sense threshold voltage V _{IN} -V _{CSN} Nominal 194 200 206 mV V _{CSN_HYS} Sense threshold hysteresis ±15 % % I _{CSN} CSN Pin input current V _{IN} -V _{CSN} =5∪W 8 µA Operating Current I _{SD} Shutdown supply current with output off 60 100 µA DIM Input Outescent supply current with output off No switching 0.16 0.3 mA DIM Input V _{DIM} Dimercial supply voltage DIM floating 4.2 V V V _{DIM, HYS} DIM input voltage High 2.5 0.3 V V _{DIM, HYS} DIM input voltage hysterisis 20 50 80 mV R _{DIM} DIM pull up resistor to Internal supply voltage 20 50 80 mV R _{DIM} I _{DIM} Dim input leakage high V _{DIM} =5V 2.8 µA Dim input leakage low V _{DIM} =5V 2.8	V _{UVLO_HYS}	UVLO hysterisis	VCC falling			0.3		7
V _{CSN} Current sense threshold voltage V _{IN} -V _{CSN} Nominal 194 200 206 mV V _{CSN,LYS} Sense threshold hysteresis ±15 % I _{CSN} CSN Pin input current V _{IN} -V _{CSN} =50mV 8 µA Operating Current I _{SD} Shutdown supply current with output off 60 100 µA OIM input current with output off No switching 0.16 0.3 mA DIM input off 0.16 0.3 mA DIM input V _{DIM} DIM input voltage High 4.2 V V _{DIM} DIM input voltage Low 0.3 V V _{DIM} DIM input voltage hysterisis 20 50 80 mV R _{DIM} DIM pull up resistor to Internal supply voltage 200 KΩ KΩ I _{DIM} DIM input leakage high V _{DIM} =5V 2.8 µA I _{DIM} DIM input leakage low V _{DIM} =5V 2.8 µA Driver R_source Gate driver source resistor V _{GS} =5.0V 6 </td <td>F_{SW}</td> <td>Max. Switching Frequency</td> <td></td> <td></td> <td></td> <td>1</td> <td></td> <td>MHz</td>	F _{SW}	Max. Switching Frequency				1		MHz
V_{CSN_HYS} Sense threshold hysteresis L _{SN} CSN Pin input current V _{IN*} V _{CSN} =50mV 8 μA μA	Current Se	ense						
I _{CSN} CSN Pin input current V _{IN} -V _{CSN} =50mV 8 μA Operating Current I _{SD} Shutdown supply current with output off 60 100 μA DIM Input Quiescent supply current with output off No switching 0.16 0.3 mA DIM Input Internal supply voltage DIM floating 4.2 V V V _{DIM} DIM input voltage High 2.5 0.3 V V _{DIM} DIM input voltage Low 0.3 V V _{DIM} DIM input voltage hysterisis 20 50 80 mV R _{DIM} DIM pull up resistor to Internal supply voltage 200 KΩ KΩ I _{DIM,H} DIM input leakage high V _{DIM} =5V 2.8 μA I _{DIM,H} DIM input leakage low V _{DIM} =5V 2.8 μA Driver 8 Ω Ω Ω R_sink Gate driver source resistor V _{OS} =5.0V 6 Ω Ω Ω Ω Q Ω Ω Ω	V _{CSN}	Current sense threshold voltage	V _{IN} -V _{CSN}	Nominal	194	200	206	mV
Coperating Current V _{IN} -V _{CSN} =5UMV 8 μA Operating Current I _{SD} Shutdown supply current with output off 60 100 μA DIM Input DIM Input V _{DIM} Input Internal supply voltage DIM floating 4.2 V V _{DIM} DIM input voltage High 2.5 — — V _{DIM} DIM input voltage Low 0.3 V V _{DIM} DIM input voltage hysterisis 20 50 80 mV R _{DIM} DIM pull up resistor to Internal supply voltage 200 KΩ KΩ I _{DIM, H} DIM input leakage high V _{DIM} =5V 2.8 μA I _{DIM, L} DIM input leakage low V _{DIM} =5V 2.8 μA Driver R_source Gate driver source resistor V _{SS} =5.0V 6 Ω R_sink Gate driver source resistor V _{SS} =5.0V 6 Ω V _{OH} Gate driver output-voltage high I _{DRV} =10mA 4.8 V V _{OL} Gate driver output-voltage low	V _{CSN_HYS}	Sense threshold hysteresis				±15		%
I_{SD}	I _{CSN}	CSN Pin input current	V _{IN} -V _{CSN} =50)mV		8		μA
No switching 0.16 0.3 mA	Operating	Current						
DIM Input	I _{SD}	Shutdown supply current				60	100	μΑ
V _{DIM}	I _{OFF}	, , ,	No switchin	g		0.16	0.3	mA
VDIM_H DIM input voltage High 2.5 0.3 V VDIM_L DIM input voltage Low 0.3 V VDIM_L DIM input voltage hysterisis 20 50 80 mV RDIM DIM pull up resistor to Internal supply voltage 200 KΩ Image: Low DIM input leakage high VDIM=5V 2.8 μA Image: Low DIM input leakage low DIM input leakage low VDIM = 0 22 μA Driver R_source Gate driver source resistor Vola = 5.0V 6 Ω R_source Gate driver source resistor Vola = 5.0V 6 Ω VOH Gate driver output-voltage high Input = 10mA 4.8 V VOH Gate driver output-voltage low Input = 10mA 0.5 V Output Switch TON_MIN Minimum on time Guarantee by Designer 100 nS Toper_MIN Minimum off time Designer 100 nS Thermal Regulation Temperature	DIM Input							
V _{DIM_L} DIM input voltage Low 0.3 V V _{DIM_HYS} DIM input voltage hysterisis 20 50 80 mV R _{DIM} DIM pull up resistor to Internal supply voltage 200 KΩ IbIM_H DIM input leakage high V _{DIM} =5V 2.8 μA IbIM_L DIM input leakage low V _{DIM} =0 22 μA Driver R_source Gate driver source resistor V _{GS} =5.0V 6 Ω R_sink Gate driver source resistor 2 Ω V _{OH} Gate driver output-voltage high I _{DRV} =10mA 4.8 V V _{OL} Gate driver output-voltage low I _{DRV} =10mA 0.5 V Output Switch Ton_MIN Minimum on time Guarantee by 100 nS Toeff_MIN Minimum off time Designer 100 nS Thermal Regulation Thermal Regulation 140 °C	V _{DIM}	Internal supply voltage	DIM floating)		4.2		V
VDIM_HYS DIM input voltage hysterisis 20 50 80 mV RDIM pull up resistor to Internal supply voltage 200 κΩ IbIM_H DIM input leakage high VDIM=5V 2.8 μA IbIM_L DIM input leakage low VDIM=5V 2.8 μA Driver R_source Gate driver leakage low VDIM=0 22 μA Driver R_source Gate driver source resistor VG 6 Ω R_sink Gate driver sink resistor 2 Ω VOH Gate driver output-voltage high IDRV=10mA 4.8 V VOL Gate driver output-voltage low IDRV=10mA 0.5 V Output Switch TON_MIN Minimum on time Guarantee by 100 nS ToFF_MIN Minimum off time Designer 100 nS Thermal Regulation Temperature	V _{DIM_H}	DIM input voltage High			2.5			
R _{DIM} DIM pull up resistor to Internal supply voltage 200 KΩ	V_{DIM_L}	DIM input voltage Low					0.3	V
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	V _{DIM_HYS}	DIM input voltage hysterisis			20	50	80	mV
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	R _{DIM}					200		ΚΩ
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	I _{DIM H}	DIM input leakage high	V _{DIM} =5V			2.8		μA
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	I _{DIM_L}	DIM input leakage low	$V_{DIM} = 0$			22		μA
R_sink Gate driver sink resistor 2 Ω V _{OH} Gate driver output-voltage high I _{DRV} =10mA 4.8 V V _{OL} Gate driver output-voltage low I _{DRV} =10mA 0.5 V Output Switch T _{ON_MIN} Minimum on time Guarantee by Designer 100 nS T _{OFF_MIN} Minimum off time Designer 100 nS Thermal Shutdown T _{REG} Thermal Regulation Temperature 140 °C	Driver		l				I.	
V _{OH} Gate driver output-voltage high I _{DRV} =10mA 4.8 V V _{OL} Gate driver output-voltage low I _{DRV} =10mA 0.5 V Output Switch T _{ON_MIN} Minimum on time Guarantee by 100 nS T _{OFF_MIN} Minimun off time Designer 100 nS Thermal Shutdown T _{REG} Thermal Regulation Temperature 140 °C	R_source	Gate driver source resistor	V _{GS} =5.0V			6		Ω
Vol Gate driver output-voltage low I _{DRV} =10mA 0.5 V Output Switch Ton_Min Minimum on time Guarantee by Designer 100 nS Thermal Shutdown Treff Thermal Regulation Temperature 140 °C	R_sink	Gate driver sink resistor				2		Ω
Output Switch Ton_MIN Minimum on time Guarantee by 100 nS Toff_MIN Minimun off time Designer 100 nS Thermal Shutdown Tres Thermal Regulation Temperature 140 °C	V _{OH}	Gate driver output-voltage high	I _{DRV} =10mA			4.8		V
Ton_MIN Minimum on time Guarantee by Designer 100 nS Toff_MIN Minimun off time Designer 100 nS Thermal Shutdown TREG Thermal Regulation Temperature 140 °C	V _{OL}	Gate driver output-voltage low I _{DRV} =1					0.5	V
Toff_MIN Minimun off time Designer 100 nS Thermal Shutdown Tress Thermal Regulation Temperature 140 °C								
Thermal Shutdown T _{REG} Thermal Regulation Temperature 140 °C	T _{ON_MIN}	Minimum on time	Guarantee	by		100		nS
Thermal Regulation Temperature	T _{OFF_MIN}	Minimun off time	Designer			100		nS
Temperature 140	Thermal Shutdown							
T _{SD} Thermal Shutdown Temperature 150 °C	T _{REG}	9				140		${\mathbb C}$
	T _{SD}	Thermal Shutdown Temperature				150		$^{\circ}$ C

Note 3: Datasheet min/max specification limits are guaranteed by design, test, or statistical analysis.

SIMPLIFIED BLOCK DIAGRAM



OPERATION DESCRIPTION

The PT4121E in conjunction with current sense resistor (R_{CS}),the inductor (L1), and MOSFET forms a self oscillating continuous-mode buck converter.

When input voltage VIN is first applied, the initial current in L1 and R_{CS} is zero and there is no output from the current sense circuit. Under this condition, the output of CS comparator is high. This turns on switch, causing current to flow from V_{IN} to ground, via R_{CS}, the LED(s),L1 and external MOSFET. The current rises at a rate determined by V_{IN} and L1 to produce a voltage ramp (VCSN) across R_{CS}. When (VIN-VCSN) > 230mV, the output of CS comparator switches low and the switch turns off. The current flowing on the R_{CS} decreases at another rate. When (VIN-VCSN) < 170mV, the switch turns on again and the mean current on the LED is determined by 200mV/R_{CS}.

The high-side current-sensing scheme and on-board current-setting circuitry minimize the number of external components while delivering LED current with ±3% accuracy, using a 1%

sense resistor. The PT4121E allows dimming with a PWM signal at the DIM input. A logic level below 0.3V at DIM forces PT4121E to turn off the LED and the logic level at DIM must be at least 2.5V to turn on the full LED current. The frequency of PWM dimming ranges from 100Hz to 20 kHz.

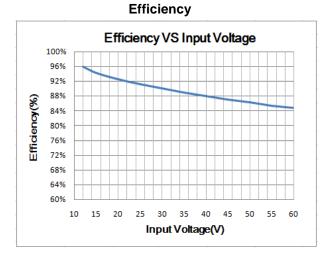
The DIM pin can be driven by an external DC voltage (V_{DIM}) to adjust the output current to a value below the nominal average value defined by R_{CS}. The DC voltage is valid from 0.5V to 2.5V. When the DC voltage is higher than 2.5V, the output current keeps constant.

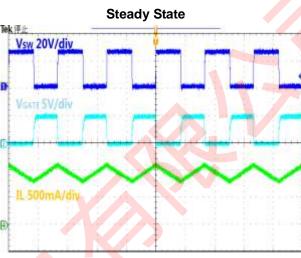
Additionally, to ensure the reliability, the PT4121E is built with an over temperature protection. If the junction temperature exceeds T_{REG}, the device will reduce output current to avoid system cause to damage.



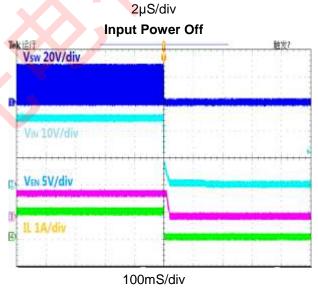


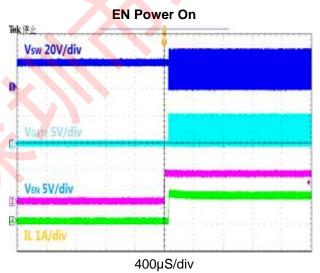
TYPICAL PERFORMANCE CHARACTERASTICS

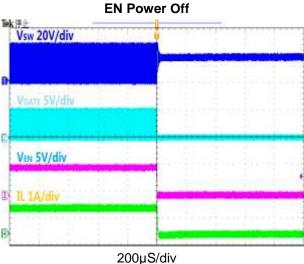














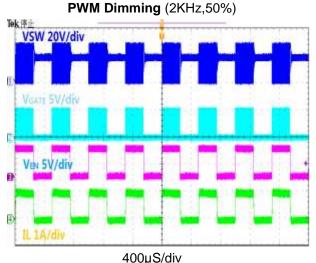


PWM Dimming (2KHz,1%)

VSW 20V/div

TYPICAL PERFORMANCE CHARACTERASTICS (continued)

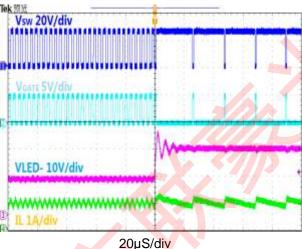
 V_{IN} =24V,3LEDs, I_{OUT} =1A, T_A =25 $^{\circ}$ C, unless otherwise noted.

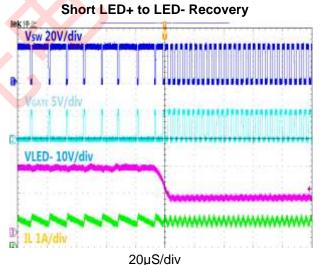


VEN 5V/div IL 1A/div

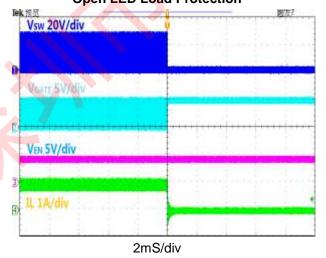
400µS/div



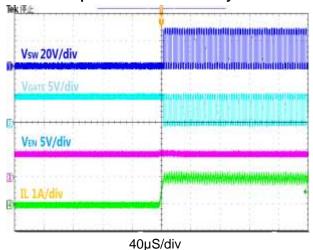








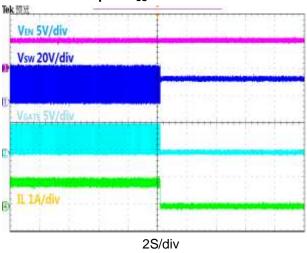
Open LED Load Recovery



TYPICAL PERFORMANCE CHARACTERASTICS (continued)

 V_{IN} =24V,3LEDs, I_{OUT} =1A, T_A =25 $^{\circ}$ C, unless otherwise noted.

Open R_{cs} Protection



APPLICATION NOTES

Setting nominal average output current with external resistor R_{CS}

The nominal average output current in the LED(s) is determined by the value of the external current sense resistor (R_{CS}) connected between VIN and CSN and is given by:

This equation is valid when DIM pin is float or applied with a voltage higher than 2.5V (must be less than 5V). Actually, R_{CS} sets the maximum average current which can be adjusted to a less one by dimming.

Output current adjustment by external DC control voltage

The DIM pin can be driven by an external DC voltage (V_{DIM}), to adjust the output current to a value below the nominal average value defined by R_{CS}. The average output current is given by:

$$I_{OUT} = \frac{0.2 \times V_{DIM}}{2.5 \times R_{CS}} (0.5 \text{V} \le \text{V}_{DIM} \le 2.5 \text{V})$$

Note that 100% brightness setting corresponds to: $(2.5V \le V_{DIM} \le 5V)$

Output current adjustment by PWM control

A Pulse Width Modulated (PWM) signal with duty

cycle PWM can be applied to the DIM pin, to adjust the output current to a value below the nominal average value set by resistor R_{CS} :

$$I_{OUT} = \frac{0.2 \times D}{R_{CS}}$$

(0≤D≤100%, 2.5V<V_{PULSE}<5.0V)

$$I_{OUT} = \frac{0.2 \times D \times V_{PULSE}}{2.5 \times R_{CS}}$$

PWM dimming provides reduced brightness by modulating the LED's forward current between 0% and 100%. The LED brightness is controlled by adjusting the relative ratios of the on time to the off time. A 25% brightness level is achieved by turning the LED on at full current for 25% of one cycle. To ensure this switching process between on and off state is invisible by human eyes, the switching frequency must be greater than 100 Hz. Above 100 Hz, the human eyes average the on and off times, seeing only an effective brightness that is proportional to the LED's on-time duty cycle. The advantage of PWM dimming is that the forward current is always constant, therefore the LED color does

PT4121E



60V Step-down High Brightness LED Controller

not vary with brightness as it does with analog dimming. Pulsing the current provides precise brightness control while preserving the color purity. The dimming frequency of PT4121E can be as high as 20 kHz.

Soft-start

An external capacitor from the DIM pin to ground will provide additional soft-start delay, by increasing the time taken for the voltage on this pin to rise to the turn-on threshold and by slowing down the rate of rise of the control voltage at the input of the comparator.

Input capacitor selection

A low ESR capacitor should be used for input decoupling, as the ESR of this capacitor appears in series with the supply source impedance and lowers overall efficiency. This capacitor has to supply the relatively high peak current to the coil and smooth the current ripple on the input supply. A minimum value of 10µF is acceptable if the DC input source is close to the device, but higher values will improve performance at lower input voltages, especially when the source impedance is high. The voltage rating should be greater than the input voltage. The input capacitor should be placed as close as possible to the IC. For maximum stability over temperature and voltage, capacitors with X7R, X5R, or better dielectric are recommended. Capacitors with Y5V dielectric are not suitable for decoupling in this application and should not be used.

Inductor selection

Lower value of inductance can result in a higher switching frequency, which causes a larger switching loss. Choose a switch frequency between 100kHz to 500kHz for most application.

According to switching frequency, inductor value can be estimated as:

$$L = \frac{(1 - V_{OUT} / V_{IN}) \times V_{OUT}}{0.3 \times I_{LED} \times fsw}$$

For higher efficiency, choose an inductor with a DC resistance as small as possible.

Output capacitor selection

For most applications, the output capacitor is not necessary. Peak to peak ripple current in the LED(s) can be reduced below 30% of the average current, if required, by adding a capacitor across the LED(s). A value of 2.2µF will meet most requirements. Proportionally lower ripple can be achieved with higher capacitor values. Note that the capacitor will not affect operating frequency or efficiency, but it will increase start-up delay and reduce the frequency of dimming, by reducing the rate of rise of LED voltage.

Thermal considerations

The over temperature protection circuitry senses the junction temperature of the die. If the junction temperature exceeds T_{REG} , the device will reduce output current to avoid system cause to damage.

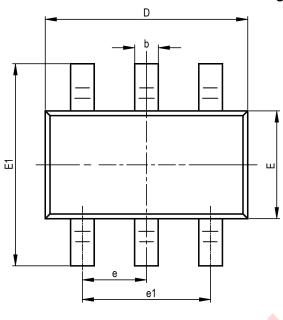
Layout considerations

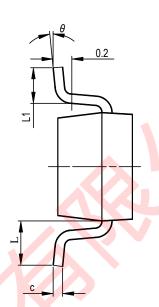
Pay careful attention to the PCB layout and component placement. R_{CS} should be placed close to the VIN pin and CSN pin in order to minimize current sense error. The input loop including input capacitor, Schottky diode, and MOSFET which should be as short as possible.

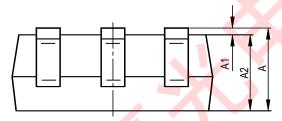




SOT23-6 Package





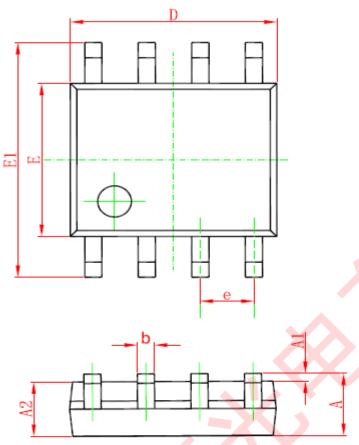


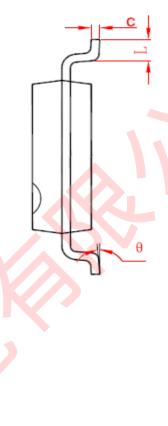
Cymbol	Millin	neters	Inches		
Symbol	Min	Max	Min	Max	
A		1.450	-	0.057	
A1	0.000	0.150	0.000	0.006	
A2	0.900	1.300	0.035	0.051	
b	0.300	0.500	0.012	0.020	
С	0.080	0.220	0.003	0.009	
D	2.820	3.020	0.111	0.119	
E	1.500	1.700	0.059	0.067	
E1	2.600	2.950	0.102	0.116	
е	0.950TYP		0.037TYP		
e1	1.800	2.000	0.071	0.079	
L	0.600REF		0.024REF		
L1	0.300	0.600	0.012	0.024	
θ	0°	8°	0°	8°	

SOP-8 Package









Symbol	Millimeters		Inches		
Symbol	Min	Max	Min	Max	
A	1.350	1.750	0.053	0.069	
A1	0.100	0.250	0.004	0.010	
A2	1.250	1.650	0.049	0.065	
b	0.330	0.510	0.013	0.020	
С	0.170	0.250	0.007	0.010	
D	4.700	5.100	0.185	0.201	
Е	3.800	4.000	0.150	0.157	
E1	5.800	6.200	0.228	0.244	
е	1.270(BSC)		0.050(BSC)		
L	0.400	1.270	0.016	0.05	
θ	0°	8°	0°	8°	

IMPORTANT NOTICE





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Only those POWTECH components which POWTECH has specifically designated as military grade or "enhanced plastic" are designed and intended for use in military/aerospace applications or environments. Buyer acknowledges and agrees that any military or aerospace use of POWTECH components which have not been so designated is solely at the Buyer's risk, and that Buyer is solely responsible for compliance with all legal and regulatory requirements in connection with such use

Unless POWTECH has specifically designated certain components which meet ISO/TS16949 requirements, mainly for automotive use, POWTECH will not be responsible for any failure of such components to meet such requirements.